

**■ ■ APPLICATION:** General Purpose Applications.

**■ ■ MAXIMUM RATINGS** (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V <sub>CB0</sub>	32	V
Collector-emitter voltage	V <sub>CEO</sub>	32	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>c</sub>	2	A
Collector Power Dissipation	P <sub>c</sub>	750	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55~150	°C


**■ ■ ELECTRICAL CHARACTERISTICS** (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h <sub>FE</sub>	82		560		V <sub>CE</sub> = 3V, I <sub>c</sub> = 500mA
Collector Cut-off Current	I <sub>CB0</sub>			0.1	μA	V <sub>CB</sub> = 32V, I <sub>E</sub> =0
Emitter Cut-off Current	I <sub>EBO</sub>			0.1	μA	V <sub>EB</sub> = 5V, I <sub>c</sub> =0
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	32			V	I <sub>c</sub> = 0.1mA, I <sub>E</sub> =0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	32			V	I <sub>c</sub> = 10mA, I <sub>B</sub> =0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5			V	I <sub>E</sub> = 0.1mA, I <sub>c</sub> =0
Base-Emitter Voltage	V <sub>BE</sub>			1	V	V <sub>CE</sub> = 2V, I <sub>c</sub> = 500mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			2	V	I <sub>c</sub> = 1500mA, I <sub>B</sub> = 30mA
Gain bandwidth product	f <sub>r</sub>		120		MHz	I <sub>c</sub> = 500mA, V <sub>CE</sub> = 2V
Common Base Output Capacitance	C <sub>ob</sub>		30		PF	V <sub>CB</sub> = 10V, I <sub>E</sub> =0, f= 1MHz

**■ ■ h<sub>FE</sub> Classification And Marking**

Classification	P	Q	R	S
h <sub>FE</sub>	82~180	120~270	180~390	270~560